

**Features** 

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PI3USB42

#### USB2.0 High-Speed (480Mbps) Signal Switch With Vbus Short Protection

 $R_{ON}$  is 4.0 $\Omega$  Typical @  $V_{DD} = 3.0V$ 

Low Crosstalk: -41dB @ 240MHz

Off Isolation: -37dB @ 240MHz

Wide -3db Bandwidth: 770MHz

Channel On Capacitance: 6.0pF

Near-Zero Propagation Delay: 250ps

VDD Operating Range: 1.8V to 4.5V

Low Bit-to-Bit Skew

A114D Specification

a Short to Vbus

representative.

USB 2.0 Compliant (High Speed and Full Speed)

Supports for 1.8V/2.5V/3.3V Logic on Control Pins

Data Pin I/O ESD: >8kV HBM Protection per JESD22-

I/O Pins Have Over-voltage Protection and Can Tolerate

Packaging (Pb-free & Green): 10-pin, UQFN (ZM10) Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

Halogen and Antimony Free. "Green" Device (Note 3)

For automotive applications requiring specific change

control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949

certified facilities), please contact us or your local Diodes

https://www.diodes.com/guality/product-definitions/

#### Description

The PI3USB42 is a single differential channel 2:1 multiplexer/demultiplexer USB 2.0 Switch. Industry leading advantages include a propagation delay of less than 250ps, resulting from its low channel resistance and I/O capacitance. The device multiplexes differential outputs from a USB Host device to one of two corresponding outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. It is designed for low bit-to-bit skew, high channel-to-channel noise isolation and is compatible with various standards, such as High Speed USB 2.0 (480Mb/s).

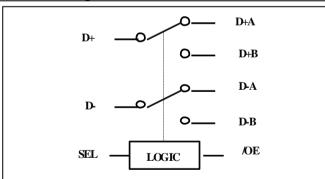
The PI3USB42 offers overvoltage protection per the USB2.0 specification. With the chip powered on or off, all I/O pins can withstand a short to Vbus (5V +/-10%). If VDD = 0V, the I/Os can still have signals present, and the signal will NOT leak through to VDD.

If the Vin (D+/-) is 0.6V greater than VDD, USB42 will turn off the switch between Input (D+/-) and output (D+A/B and D-A/B).

## Application(s)

- Route Signals for USB 2.0
- Cell Phones, PDA, Digital Camera and Notebooks
- LCD Monitors, TVs, Set-top Boxes
- Portable Devices

## **Block Diagram**



#### **Table 1. Logic Function Table**

/OE	SEL	Function
Н	Х	I/O's = Hi-Z
L	L	D(+/-) to D(+/-)A
L	Н	D(+/-) to D(+/-)B

Notes:

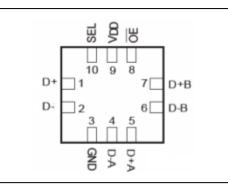
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</li>

<sup>1.</sup> No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.





# **Pin Configuration**



# **Pin Description**

Pin Number	Pin Name	Description	
1	D+	USB Data bus	
2	D-	USB Data bus	
3	GND	Ground	
4	D-A	Multiplexed Source Inputs	
5	D+A	Multiplexed Source Inputs	
6	D-B	Multiplexed Source Inputs	
7	D+B	Multiplexed Source Inputs	
8	/OE	Switch Enable	
9	V <sub>DD</sub>	Positive Power Supply	
10	SEL	Switch Select	



**Maximum Ratings** 



PI3USB42

Storage Temperature	65℃ to +150℃
Junction Temperature	
Supply Voltage to Ground Potential	0.5V to +5V
Control Input Voltage	0.5V to 4.6V
DC Switch Voltage (D+, D-, D+A, D-A, D+B and D-B)	0.5V to 5.25V
DC Output Current	120mA
Power Dissipation	0.5W
ESD (HBM)	>8kV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

## **Recommended Operating Conditions**

Symbol	Parameter	Min.	Тур.	Max.	Unit
$V_{DD}$	Operating Voltage	1.8		4.5	
V <sub>CNTRL</sub> <sup>(1)</sup>	Control Input Voltage	0		4.3	V
VINPUT	Switch Input Voltage	-0.5		V <sub>DD</sub> +0.5	
T <sub>A</sub>	Operating Temperature	-40		105	°C

Notes:

1. The control input must be held high or low and it must not float.

#### **DC Electrical Characteristics**

$\frac{1}{Parameter}$	+105°C, $V_{DD} = 3.0V - 4.5V$ Description	Test Conditions <sup>(1)</sup>	Min.	<b>Typ.</b> <sup>(2)</sup>	Max.	Unit
V <sub>IH</sub>	Input High Voltage	Guaranteed High Level	1.2			
V <sub>IL</sub>	Input Low Voltage	Guaranteed Low Level			0.60	V
V <sub>IK</sub>	Clamp Diode Voltage	$V_{DD} = Max., I_{SEL} = -18mA$		-0.7	-1.2	
I <sub>IH</sub>	Input High Current	$V_{DD} = Max., V_{SEL} = V_{DD}$			±100	A
I <sub>IL</sub>	Input Low Current	$V_{DD} = Max., V_{SEL} = GND$		±100		nA
R <sub>ON</sub>	Switch On-Resistance <sup>(3)</sup>	$\label{eq:VDD} \begin{split} V_{\text{DD}} &= Min., 0 \leq V_{\text{INPUT}} \leq \!\! 0.4V, \\ I_{\text{INPUT}} &= -40 mA \end{split}$		4.0	5.5	
R <sub>FLAT(ON)</sub>	On-Resistance Flatness <sup>(3)</sup>	$\label{eq:VDD} \begin{split} V_{\text{DD}} &= Min., 0 \leq V_{\text{INPUT}} \leq \!\! 0.4V, \\ I_{\text{INPUT}} &= -40 \text{mA} \end{split}$		0.25		Ω
△R <sub>ON</sub>	On-Resistance match from center ports to any other port <sup>(3)</sup>	$\label{eq:VDD} \begin{split} V_{\rm DD} &= Min., 0 \leq V_{\rm INPUT} \leq \!\! 0.4V, \\ I_{\rm INPUT} &= -40mA \end{split}$		0.1	1.0	
I <sub>OZ</sub>	Output leakage current when port is off	$V_{\rm DD} = 4.5V, 0 \leq V_{\rm INPUT} \leq \!\! 0.4V$			±100	nA
I <sub>OFF</sub>	Power-Off Leakage Current	$V_{INPUT} = 0V \sim 4.3V, V_{DD} = 0V$			100	nA

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

2.  $V_{DD} = 3.0 - 4.5V$ ,  $T_A = 25^{\circ}C$  ambient and maximum loading.

3. Measured by the voltage drop between D and Dn pin at indicated current through the Switch On-Resistance is determined by the lower of the voltages on the two (D, Dn) pins.

## **Power Supply Characteristics**

$T_{\rm A} = -40^{\circ}$ C to $+105^{\circ}$ C, $V_{\rm DD} = 3.0$ V $- 4.5$ V						
Parameter	Description	Test Conditions <sup>(1)</sup>	Min.	Тур.	Max.	Unit.
I <sub>CC</sub>	Quiescent Power Supply current	$V_{DD} = Max., V_{SEL} = V_{DD} \text{ or}$ GND			100	nA
I <sub>CCT</sub>	Increase in $I_{CC}$ Current per	$V_{CNTRL} = 1.8V, V_{DD} = 4.5V$		5.8	15	μΑ





Parameter	Description	Test Conditions <sup>(1)</sup>	Min.	Тур.	Max.	Unit.
Control Voltage and V <sub>DD</sub>						

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

Capacitance						
$T_A = 25^{\circ}C, V_{DD} = 3.0V, f = 1MHz$						
Parameters	Description	Test Conditions	Min.	Тур.	Max.	Units
C <sub>CNTRL</sub>	Control logic pin Input Capacitance			6.0		
C <sub>OFF</sub>	Switch Capacitance, Switch OFF	$V_{\text{SEL}} = 0V$		1.9		pF
C <sub>ON</sub>	Switch Capacitance, Switch ON			6.0		

## **Dynamic Electrical Characteristics Over the Operating Range**

$T_A = 25^{\circ}C, V_{DD}$	= 3.0 V					
Parameters	Description	Test Conditions <sup>(1)</sup>	M in.	Тур.	Max.	Units
XTALK	Crosstalk	$R_{L} = 50\Omega, f = 240MHz$		-41		dB
OIRR	OFF Isolation	$K_{\rm L} = 5002, 1 = 240 {\rm MHz}$		-37		UD
BW	–3dB Bandwidth	$R_L = 50\Omega$		770		MHz

# **Switching Characteristics**

Parameters	Description	Test Conditions <sup>(1)</sup>	Min	Тур.	Max	Units
t <sub>PD</sub>	Propagation Delay <sup>(2,3)</sup>			0.25		
t <sub>PZH</sub> , t <sub>PZL</sub>	Line Enable Time - SEL to D(+/-), D(+/-)n	See Test Circuit for Electrical Characteristics		25		ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	Line Disable Time - SEL to D(+/-), D(+/-)n	Electrical Characteristics		4		
t <sub>BBM</sub>	Break-Before-Make			7		ns
	Output skew, bit-to-bit	$V_{DD} = 3V$			35	
t <sub>SKb-b</sub>	(opposite transition of the same output $(t_{PHL}-t_{PLH})^{(2)}$	$V_{\rm DD} = 4V$			60	ps

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Guaranteed by design.

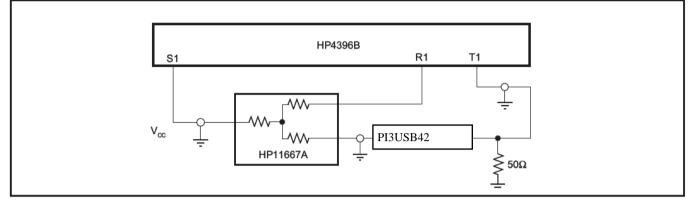
3. The switch contributes no propagational delay other than the RC delay of the On-Resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25ns for 10pF load. Since this time constant is much smaller than the rise/fall times of typical driving signals, it adds very little propagational delay to the system. Propagational delay of the switch when used in a system is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.



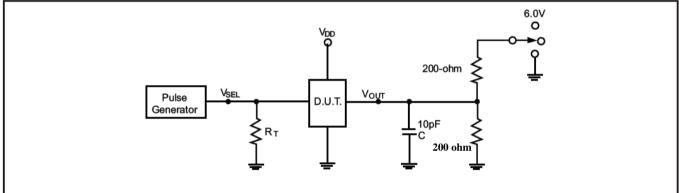


# Test Circuits and Test Diagramming

#### Test Circuit for Dynamic Electrical Characteristics



## **Test Circuit for Electrical Characteristics**



Notes:

 $C_L$  = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to  $Z_{OUT}$  of the Pulse Generator

Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. All input impulses are supplied by generators having the following characteristics: PRR  $\leq$  MHz, ZO = 50 $\Omega$ , tR  $\leq$  2.5ns, tF  $\leq$  2.5ns.

The outputs are measured one at a time with on transition per measurement.

#### **Table 2. Switch Positions**

Test	Switch
t <sub>PLZ</sub> , t <sub>PZL</sub> (output on I-side)	6.0V
t <sub>PHZ</sub> , t <sub>PZH</sub> (output on I-side)	GND
Prop Delay	Open

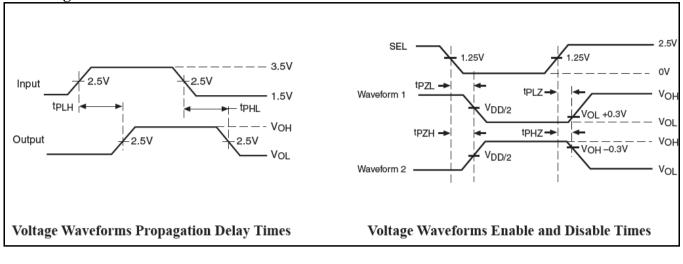


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PI3USB42

# **Switching Waveforms**



# **Applications Information**

#### **Logic Inputs**

The logic control inputs can be driven up to +4.3V regardless of the supply voltage. For example, given a +3.3V supply, the output enables or select pins may be driven to low to 0V and high to 4.3V.

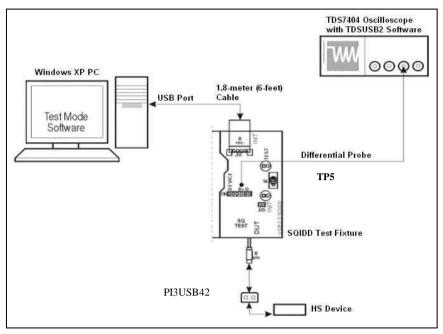
#### **Power Supply Sequencing**

Proper power supply sequencing is recommended for all CMOS devices. Always apply VDD and GND before applying signals to input/output or control pin.

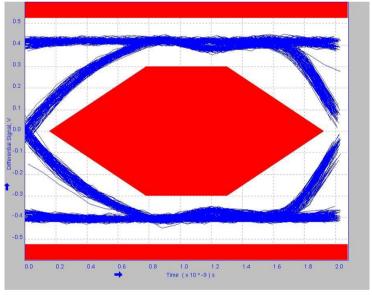




## **Eye Diagram Measurement**



USB2.0 High-speed (480Mbps) Signal Integrity Test Setup

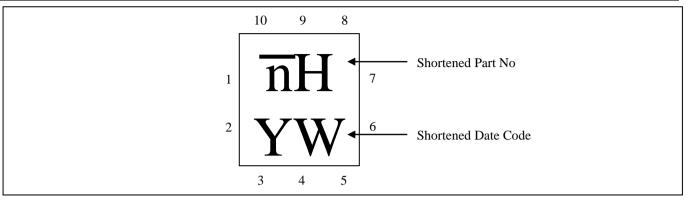


High Speed Signal Ouality Eve Diagram Test ( $V_{DD} = 3.3V$ )





# **Part Marking**



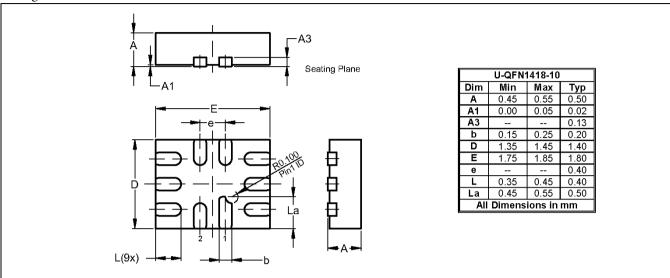




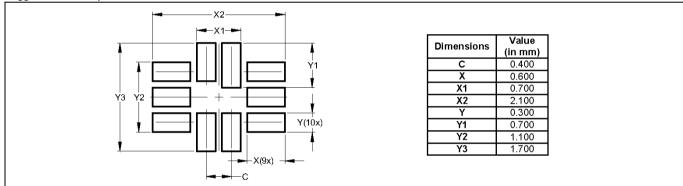
## Packaging Mechanical

10-UQFN (ZM)





Suggested Pad Layout



#### ALL DIMENSIONS ARE NOMINAL VALUES SHOWN IN MILLIMETERS

Note: The suggested land pattern dimensions have been provided for reference only, as actual pad layouts may vary depending on application. These numbers may be modified based on user equipment capability or fabrication criteria. A more robust pattern may be desired for wave soldering and is calculated by adding 0.2 mm to the 'Z' dimension. For further information, please reference document IPC-7351A, Naming Convention for Standard SMT Land Patterns, and for International grid details, please see document IEC, Publication 97.

#### For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

## **Ordering Information**

Orderable Part Number	Package Code	Package Description
PI3USB42ZMEX	ZM	10-contact, Ultra-thin Quad Flat No-Lead (UQFN)

#### Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. E = Pb-free and Green

5. X suffix = Tape/Reel





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